

Product Overview

NTBG015N065SC1: Silicon Carbide MOSFET, N-Channel, 650V, 15.3 mΩ , D2PAK-7L

For complete documentation, see the data sheet.

Silicon Carbide (SiC) MOSFET uses a completely new technology that provide superior switching performance and higher reliability compared to Silicon. In addition, the low ON resistance and compact chip size ensure low capacitance and gate charge. Consequently, system benefits include highest efficiency, faster operation frequency, increased power density, reduced EMI, and reduced system size.

Features

- Low RDSon
- High Junction Temperature
- 100% UIL Tested
- RoHS Compliant
- High Speed Switching and Low Capacitance
- 650V rated
- Max RDS(on) = 18.4 mΩ at Vgs = 18V, Id = 60A

Benefits

- 15.3 mΩ
- Tj = 175°C

Applications

- DC-DC Converter
- Boost Inverter

End Products

- UPS
- Solar
- Power Supply

Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	Channel Polarity	Configuration	Blocking Voltage BV _{DSS} (V)	I _{D(max)} (A)	R _{DS(on)} Typ @ 25°C (mΩ)	Q _g Total (C)	Output Capacitance (C)	T _j Max (°C)	Package Type
NTBG015N065SC1	15.6881	Pb-free Halide free non AEC-Q and PPAP	Active	N-Channel	Single	650	176	15.3	250	397	175	D2PAK7 (TO-263-7L HV)

For more information please contact your local sales support at www.onsemi.com.

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